



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



## Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



# MX25R6435F

**ULTRA LOW POWER, 64M-BIT [x 1/x 2/x 4]  
CMOS MXSMIO<sup>®</sup> (SERIAL MULTI I/O)  
FLASH MEMORY**

## ***Key Features***

- *Ultra Low Power Mode and High Performance Mode*
- *Wide Range VCC 1.65V-3.6V for Read, Erase and Program Operations*
- *Unique ID and Secure OTP Support*
- *Multi I/O Support - Single I/O, Dual I/O and Quad I/O*
- *Program Suspend/Resume & Erase Suspend/Resume*

## Contents

<b>1. FEATURES</b> .....	<b>4</b>
<b>2. GENERAL DESCRIPTION</b> .....	<b>6</b>
Table 1. Additional Feature .....	7
<b>3. PIN CONFIGURATIONS</b> .....	<b>8</b>
<b>4. PIN DESCRIPTION</b> .....	<b>8</b>
<b>5. BLOCK DIAGRAM</b> .....	<b>9</b>
<b>6. DATA PROTECTION</b> .....	<b>10</b>
Table 2. Protected Area Sizes .....	11
Table 3. 8K-bit Secured OTP Definition .....	12
<b>7. MEMORY ORGANIZATION</b> .....	<b>13</b>
Table 4. Memory Organization .....	13
<b>8. DEVICE OPERATION</b> .....	<b>14</b>
<b>9. HOLD FEATURE</b> .....	<b>16</b>
<b>10. COMMAND DESCRIPTION</b> .....	<b>17</b>
Table 5. Command Set.....	17
10-1. Write Enable (WREN).....	20
10-2. Write Disable (WRDI).....	21
10-3. Read Identification (RDID).....	22
10-4. Read Electronic Signature (RES) .....	23
10-5. Read Electronic Manufacturer ID & Device ID (REMS).....	24
10-6. ID Read.....	25
Table 6. ID Definitions .....	25
10-7. Read Status Register (RDSR).....	26
10-8. Read Configuration Register (RDCR).....	27
10-9. Write Status Register (WRSR).....	32
Table 7. Protection Modes.....	33
10-10. Read Data Bytes (READ) .....	36
10-11. Read Data Bytes at Higher Speed (FAST_READ) .....	37
10-12. Dual Read Mode (DREAD).....	38
10-13. 2 x I/O Read Mode (2READ) .....	39
10-14. Quad Read Mode (QREAD) .....	40
10-15. 4 x I/O Read Mode (4READ) .....	41
10-16. Burst Read.....	43
10-17. Performance Enhance Mode .....	44
10-18. Sector Erase (SE).....	46
10-19. Block Erase (BE32K) .....	47
10-20. Block Erase (BE) .....	48
10-21. Chip Erase (CE).....	49
10-22. Page Program (PP) .....	50
10-23. 4 x I/O Page Program (4PP).....	51
10-24. Deep Power-down (DP).....	52
10-25. Enter Secured OTP (ENSO).....	53

10-26. Exit Secured OTP (EXSO).....	53
10-27. Read Security Register (RDSCUR).....	53
Table 8. Security Register Definition.....	54
10-28. Write Security Register (WRSCUR).....	54
10-29. Program Suspend and Erase Suspend.....	55
Table 9. Readable Area of Memory While a Program or Erase Operation is Suspended.....	55
Table 10. Acceptable Commands During Program/Erase Suspend after tPSL/tESL.....	55
Table 11. Acceptable Commands During Suspend (tPSL/tESL not required).....	56
10-30. Program Resume and Erase Resume.....	57
10-31. No Operation (NOP).....	58
10-32. Software Reset (Reset-Enable (RSTEN) and Reset (RST)).....	58
10-33. High Voltage Operation.....	60
10-34. Read SFDP Mode (RDSFDP).....	61
<b>11. RESET.....</b>	<b>62</b>
Table 12. Reset Timing-(Power On).....	62
Table 13. Reset Timing-(Other Operation).....	62
<b>12. POWER-ON STATE.....</b>	<b>63</b>
<b>13. ELECTRICAL SPECIFICATIONS.....</b>	<b>64</b>
Table 14. Absolute Maximum Ratings.....	64
Table 15. Capacitance.....	64
Table 16. DC Characteristics.....	66
Table 17. AC Characteristics.....	68
<b>14. OPERATING CONDITIONS.....</b>	<b>72</b>
Table 18. Power-Up/Down Voltage and Timing.....	74
14-1. Initial Delivery State.....	74
<b>15. ERASE AND PROGRAMMING PERFORMANCE.....</b>	<b>75</b>
<b>16. LATCH-UP CHARACTERISTICS.....</b>	<b>76</b>
<b>17. ORDERING INFORMATION.....</b>	<b>77</b>
<b>18. PART NAME DESCRIPTION.....</b>	<b>78</b>
<b>19. PACKAGE INFORMATION.....</b>	<b>79</b>
<b>20. REVISION HISTORY.....</b>	<b>83</b>

---

## Ultra Low Power 64M-BIT [x 1/x 2/x 4] CMOS MXSMIO® (SERIAL MULTI I/O) FLASH MEMORY

### 1. FEATURES

#### GENERAL

- Supports Serial Peripheral Interface -- Mode 0 and Mode 3
- 67,108,864 x 1 bit structure or 33,554,432 x 2 bits (two I/O mode) structure or 16,777,216 x 4 bits (four I/O mode) structure
- Equal Sectors with 4K byte each or Equal Blocks with 32K/64K byte each
  - Any Block can be erased individually
- Single Power Supply Operation
  - Operation Voltage: 1.65V-3.6V for Read, Erase and Program Operations
- Latch-up protected to 100mA from -1V to Vcc +1V

#### PERFORMANCE

- High Performance
  - Fast read
    - 1 I/O: 80MHz with 8 dummy cycles
    - 2 I/O: 80MHz with 4 dummy cycles, equivalent to 160MHz
    - 4 I/O: 80MHz with 2+4 dummy cycles, equivalent to 320MHz
  - Fast program and erase time
  - 8/16/32/64 byte Wrap-Around Burst Read Mode
- Ultra Low Power Consumption
- Minimum 100,000 erase/program cycles
- 20 years data retention

#### SOFTWARE FEATURES

- Input Data Format
  - 1-byte Command code
- Advanced Security Features
  - Block lock protection
  - The BP0-BP3 status bit defines the size of the area to be software protection against program and erase instructions
- Additional 8K bits secured OTP
  - Features unique identifier.
  - Factory locked identifiable and customer lockable
- Auto Erase and Auto Program Algorithm
  - Automatically erases and verifies data at selected sector or block
  - Automatically programs and verifies data at selected page by an internal algorithm that automatically times the program pulse widths (Any page to be programmed should have page in the erased state first)
- Status Register Feature
- Command Reset
- Program/Erase Suspend and Program/Erase Resume
- Electronic Identification
  - JEDEC 1-byte manufacturer ID and 2-byte device ID
  - RES command for 1-byte Device ID
  - REMS command for 1-byte manufacturer ID and 1-byte device ID
- Support Serial Flash Discoverable Parameters (SFDP) mode
- Support Unique ID (Please contact local Macronix sales for detail information)

#### **HARDWARE FEATURES**

- SCLK Input
  - Serial clock input
- SI/SIO0
  - Serial Data Input or Serial Data Input/Output for 2 x I/O read mode and 4 x I/O read mode
- SO/SIO1
  - Serial Data Output or Serial Data Input/Output for 2 x I/O read mode and 4 x I/O read mode
- WP#/SIO2
  - Hardware write protection or serial data Input/Output for 4 x I/O read mode
- RESET#/SIO3 \* or HOLD#/SIO3 \*
  - Hardware Reset pin or Serial input & Output for 4 x I/O read mode
  - or
  - HOLD feature, to pause the device without deselecting the device or Serial input & Output for 4 x I/O read mode
  - \* **Depends on part number options**
- PACKAGE
  - 8-pin SOP (200mil)
  - 8-land WSON (6x5mm)
  - 8-land USON (4x4mm)
  - 22-ball WLCSP (3-2-3 Ball Array)
  - **All devices are RoHS Compliant and Halogen-free**

## 2. GENERAL DESCRIPTION

MX25R6435F is 64Mb bits Serial NOR Flash memory, which is configured as 8,388,608 x 8 internally. When it is in four I/O mode, the structure becomes 16,777,216 bits x 4 or 33,554,432 bits x 2. MX25R6435F feature a serial peripheral interface and software protocol allowing operation on a simple 3-wire bus while it is in single I/O mode. The three bus signals are a clock input (SCLK), a serial data input (SI), and a serial data output (SO). Serial access to the device is enabled by CS# input.

When it is in two I/O read mode, the SI pin and SO pin become SIO0 pin and SIO1 pin for address/dummy bits input and data output. When it is in four I/O read mode, the SI pin, SO pin, WP# pin and RESET#/HOLD# pin become SIO0 pin, SIO1 pin, SIO2 pin and SIO3 pin for address/dummy bits input and data output.

The MX25R6435F MXSMIO<sup>®</sup> (Serial Multi I/O) provides sequential read operation on whole chip.

After program/erase command is issued, auto program/erase algorithms which program/erase and verify the specified page or sector/block locations will be executed. Program command is executed on byte basis, or page (256 bytes) basis, or word basis for erase command is executed on sector (4K-byte) or block (32K-byte), or block (64K-byte), or whole chip basis.

To provide user with ease of interface, a status register is included to indicate the status of the chip. The status read command can be issued to detect completion status of a program or erase operation via WIP bit.

Advanced security features enhance the protection and security functions, please see security features section for more details.

The MX25R6435F utilizes Macronix's proprietary memory cell, which reliably stores memory contents even after 100,000 program and erase cycles.

**Table 1. Additional Feature**

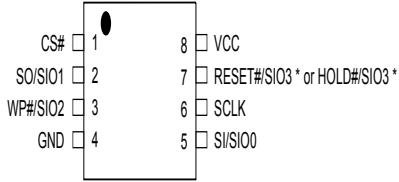
<b>Protection and Security</b>	<b>MX25R6435F</b>
Flexible Block Protection (BP0-BP3)	√
8K-bit security OTP	√

Fast Read Performance	Ultra Low Power Mode (Configuration Register-2 bit1= 0)					High Performance Mode (Configuration Register-2 bit1= 1)				
	1 I/O	1I/2O	2 I/O	1I/4O	4 I/O	1 I/O	1I/2O	2 I/O	1I/4O	4 I/O
I/O	1 I/O	1I/2O	2 I/O	1I/4O	4 I/O	1 I/O	1I/2O	2 I/O	1I/4O	4 I/O
Dummy Cycle	8	8	4	8	6	8	8	4	8	6
Frequency	33MHz	8MHz	8MHz	8MHz	8MHz	80MHz	80MHz	80MHz	80MHz	80MHz

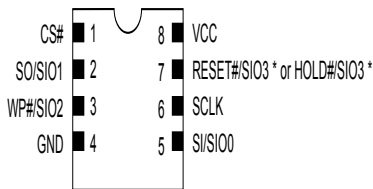


### 3. PIN CONFIGURATIONS

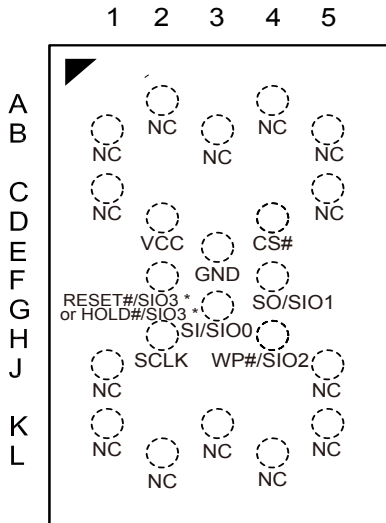
#### 8-PIN SOP (200mil)



#### 8-LAND WSON (6x5mm), USON (4x4mm)



#### 22-WLCSP TOP View



\* Depends on part number options.

### 4. PIN DESCRIPTION

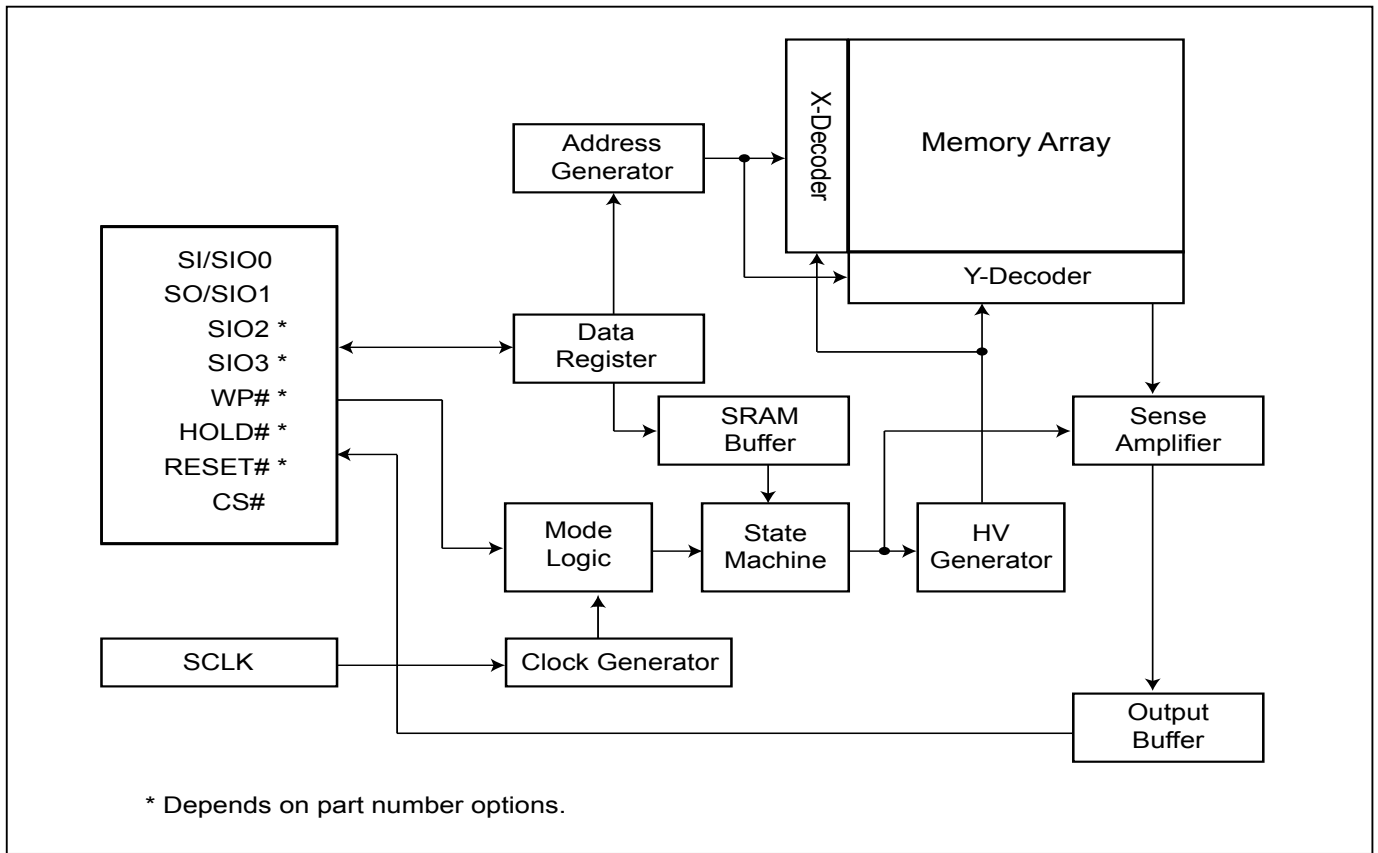
SYMBOL	DESCRIPTION
CS#	Chip Select
SI/SIO0	Serial Data Input (for 1 x I/O)/ Serial Data Input & Output (for 4xI/O read mode)
SO/SIO1	Serial Data Output (for 1 x I/O)/ Serial Data Input & Output (for 4xI/O read mode)
SCLK	Clock Input
WP#/SIO2	Write Protection Active Low or Serial Data Input & Output (for 4xI/O read mode)
RESET#/SIO3 *	Hardware Reset Pin Active low or Serial Data Input & Output (for 4xI/O read mode)
HOLD#/SIO3 *	To pause the device without deselecting the device or Serial Data Input & Output (for 4xI/O read mode)
VCC	Power Supply
GND	Ground

\* Depends on part number options.

#### Note:

1. RESET#, HOLD# and WP# with internal pull high circuit.

**5. BLOCK DIAGRAM**



## 6. DATA PROTECTION

During power transition, there may be some false system level signals which result in inadvertent erasure or programming. The device is designed to protect itself from these accidental write cycles.

The state machine will be reset as standby mode automatically during power up. In addition, the control register architecture of the device constrains that the memory contents can only be changed after specific command sequences have completed successfully.

In the following, there are several features to protect the system from the accidental write cycles during VCC power-up and power-down or from system noise.

- Power-on reset: to avoid sudden power switch by system power supply transition, the power-on reset may protect the Flash.
- Valid command length checking: The command length will be checked whether it is at byte base and completed on byte boundary.
- Write Enable (WREN) command: WREN command is required to set the Write Enable Latch bit (WEL) before issuing other commands to change data.
- Deep Power Down Mode: By entering deep power down mode, the flash device is under protected from writing all commands except toggling the CS#. For more detail please see "[10-24. Deep Power-down \(DP\)](#)".
- Advanced Security Features: there are some protection and security features which protect content from inadvertent write and hostile access.

### I. Block lock protection

- The Software Protected Mode (SPM) use (BP3, BP2, BP1, BP0) bits to allow part of memory to be protected as read only. The protected area definition is shown as "[Table 2. Protected Area Sizes](#)", the protected areas are more flexible which may protect various area by setting value of BP0-BP3 bits.
- The Hardware Protected Mode (HPM) use WP#/SIO2 to protect the (BP3, BP2, BP1, BP0) bits and Status Register Write Protect (SRWD) bit. If the system goes into four I/O mode, the feature of HPM will be disabled.

**Table 2. Protected Area Sizes**

**Protected Area Sizes (TB bit = 0)**

Status bit				Protect Level
BP3	BP2	BP1	BP0	64Mb
0	0	0	0	0 (none)
0	0	0	1	1 (1block, block 127th)
0	0	1	0	2 (2blocks, block 126th-127th)
0	0	1	1	3 (4blocks, block 124th-127th)
0	1	0	0	4 (8blocks, block 120th-127th)
0	1	0	1	5 (16blocks, block 112th-127th)
0	1	1	0	6 (32blocks, block 96th-127th)
0	1	1	1	7 (64blocks, block 64th-127th)
1	0	0	0	8 (128blocks, protect all)
1	0	0	1	9 (128blocks, protect all)
1	0	1	0	10 (128blocks, protect all)
1	0	1	1	11 (128blocks, protect all)
1	1	0	0	12 (128blocks, protect all)
1	1	0	1	13 (128blocks, protect all)
1	1	1	0	14 (128blocks, protect all)
1	1	1	1	15 (128blocks, protect all)

**Protected Area Sizes (TB bit = 1)**

Status bit				Protect Level
BP3	BP2	BP1	BP0	64Mb
0	0	0	0	0 (none)
0	0	0	1	1 (1block, block 0th)
0	0	1	0	2 (2blocks, block 0th-1st)
0	0	1	1	3 (4blocks, block 0th-3rd)
0	1	0	0	4 (8blocks, block 0th-7th)
0	1	0	1	5 (16blocks, block 0th-15th)
0	1	1	0	6 (32blocks, block 0th-31st)
0	1	1	1	7 (64blocks, block 0th-63rd)
1	0	0	0	8 (128blocks, protect all)
1	0	0	1	9 (128blocks, protect all)
1	0	1	0	10 (128blocks, protect all)
1	0	1	1	11 (128blocks, protect all)
1	1	0	0	12 (128blocks, protect all)
1	1	0	1	13 (128blocks, protect all)
1	1	1	0	14 (128blocks, protect all)
1	1	1	1	15 (128blocks, protect all)

**Note:** The device is ready to accept a Chip Erase instruction if, and only if, all Block Protect (BP3, BP2, BP1, BP0) are 0.

**II. Additional 8K-bit secured OTP** for unique identifier: to provide 8K-bit One-Time Program area for setting device unique serial number - Which may be set by factory or system maker.

The 8K-bit secured OTP area is composed of two rows of 4K-bit. Customer could lock the first 4K-bit OTP area and factory could lock the other.

- Security register bit 0 indicates whether the second 4K-bit is locked by factory or not.
- Customer may lock-down the customer lockable secured OTP by writing WRSCUR(write security register) command to set customer lock-down bit1 as "1". Please refer to "[Table 8. Security Register Definition](#)" for security register bit definition and "[Table 3. 8K-bit Secured OTP Definition](#)" for address range definition.
- To program 8K-bit secured OTP by entering secured OTP mode (with ENSO command), and going through normal program procedure, and then exiting secured OTP mode by writing EXSO command.

**Note:** Once lock-down whatever by factory or customer, the corresponding secured area cannot be changed any more. While in 8K-bit Secured OTP mode, array access is not allowed.

**Table 3. 8K-bit Secured OTP Definition**

Address range	Size	Customer Lock	Standard Factory Lock
xxx000~xxx1FF	4096-bit	Determined by customer	N/A
xxx200~xxx3FF	4096-bit	N/A	Determined by factory

**7. MEMORY ORGANIZATION**

**Table 4. Memory Organization**

Block(64K-byte)	Block(32K-byte)	Sector (4K-byte)	Address Range	
127	255	2047	7FF000h	7FFFFFFh
		⋮		
		2040	7F8000h	7F8FFFh
	254	2039	7F7000h	7F7FFFh
		⋮		
		2032	7F0000h	7F0FFFh
126	253	2031	7EF000h	7EFFFFh
		⋮		
		2024	7E8000h	7E8FFFh
	252	2023	7E7000h	7E7FFFh
		⋮		
		2016	7E0000h	7E0FFFh
125	251	2015	7DF000h	7DFFFFh
		⋮		
		2008	7D8000h	7D8FFFh
	250	2007	7D7000h	7D7FFFh
		⋮		
		2000	7D0000h	7D0FFFh

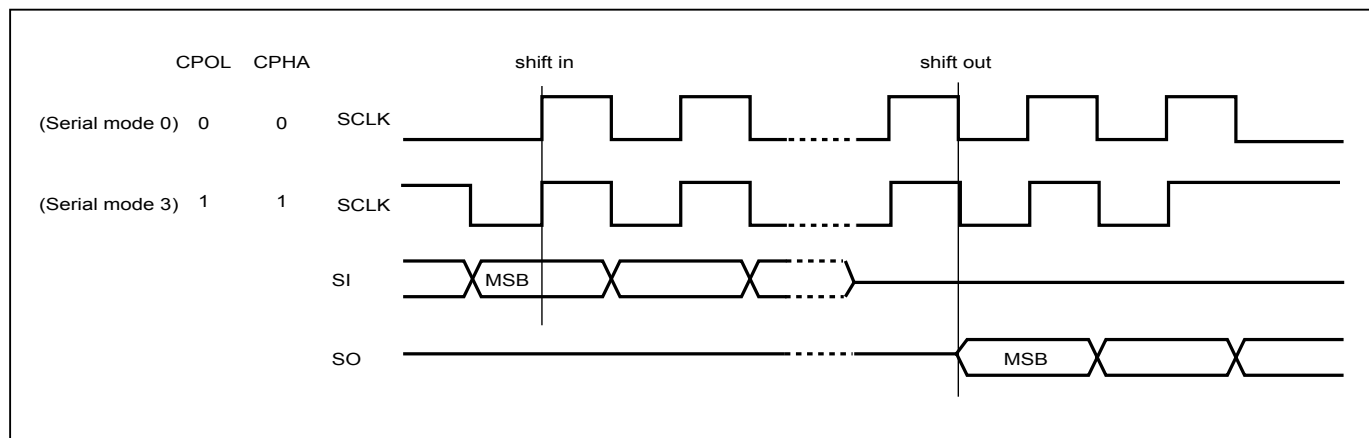


2	5	47	02F000h	02FFFFh
		⋮		
		40	028000h	028FFFh
1	4	39	027000h	027FFFh
		⋮		
		32	020000h	020FFFh
1	3	31	01F000h	01FFFFh
		⋮		
		24	018000h	018FFFh
	2	23	017000h	017FFFh
		⋮		
		16	010000h	010FFFh
0	1	15	00F000h	00FFFFh
		⋮		
		8	008000h	008FFFh
	0	7	007000h	007FFFh
		⋮		
		0	000000h	000FFFh

## 8. DEVICE OPERATION

1. Before a command is issued, status register should be checked to ensure device is ready for the intended operation.
2. When incorrect command is inputted to this device, it enters standby mode and remains in standby mode until next CS# falling edge. In standby mode, SO pin of the device is High-Z.
3. When correct command is inputted to this device, it enters active mode and remains in active mode until next CS# rising edge.
4. Input data is latched on the rising edge of Serial Clock (SCLK) and data shifts out on the falling edge of SCLK. The difference of Serial mode 0 and mode 3 is shown as "[Figure 1. Serial Modes Supported](#)".
5. For the following instructions: RDID, RDSR, RDCR, RDSCUR, READ, FAST\_READ, DREAD, 2READ, 4READ, QREAD, RDSFDP, RES, REMS, the shifted-in instruction sequence is followed by a data-out sequence. After any bit of data being shifted out, the CS# can be high. For the following instructions: WREN, WRDI, WRSR, SE, BE32K, BE, CE, PP, 4PP, DP, ENSO, EXSO, WRSCUR, SUSPEND, RESUME, NOP, RSTEN, RST, the CS# must go high exactly at the byte boundary; otherwise, the instruction will be rejected and not executed.
6. While a Write Status Register, Program or Erase operation is in progress, access to the memory array is neglected and will not affect the current operation of Write Status Register, Program, Erase.

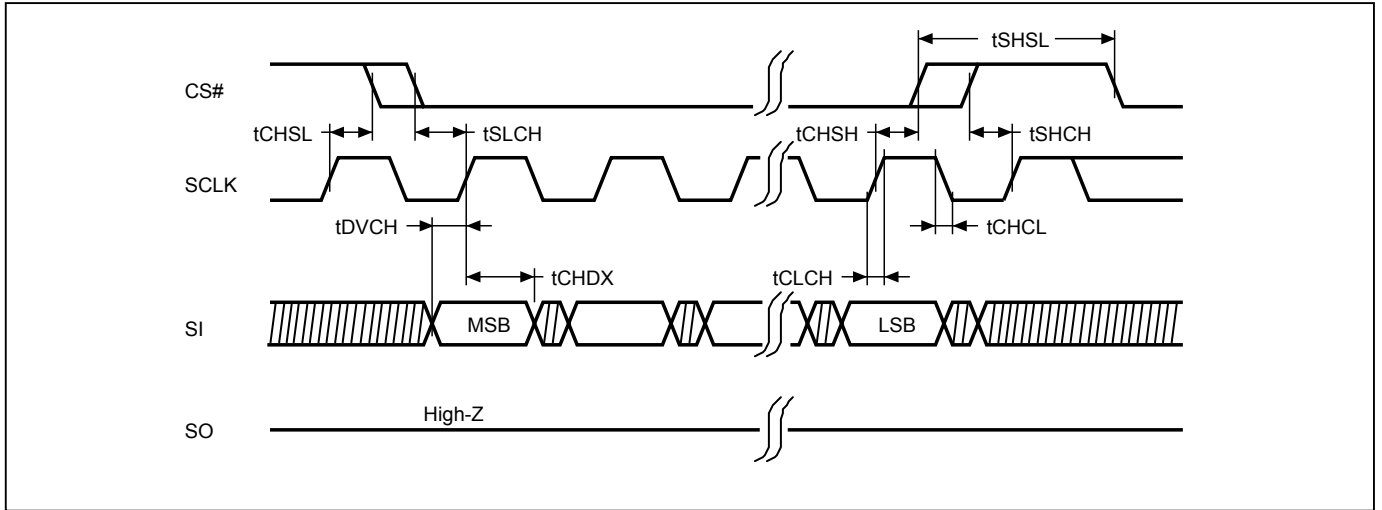
**Figure 1. Serial Modes Supported**



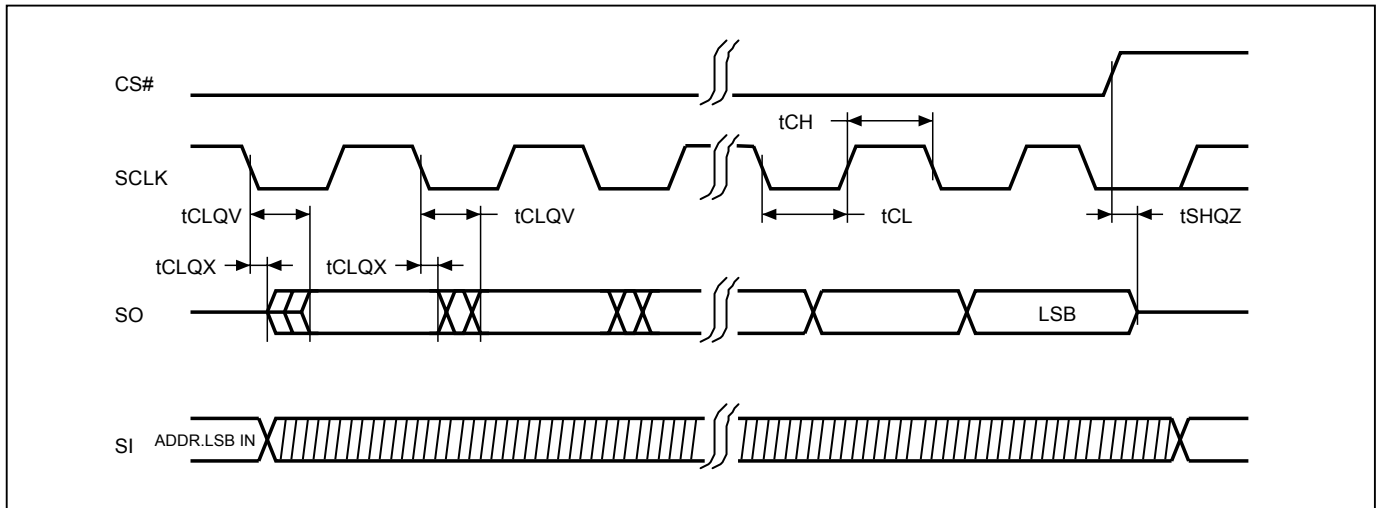
**Note:**

CPOL indicates clock polarity of Serial master, CPOL=1 for SCLK high while idle, CPOL=0 for SCLK low while not transmitting. CPHA indicates clock phase. The combination of CPOL bit and CPHA bit decides which Serial mode is supported.

**Figure 2. Serial Input Timing**



**Figure 3. Output Timing**



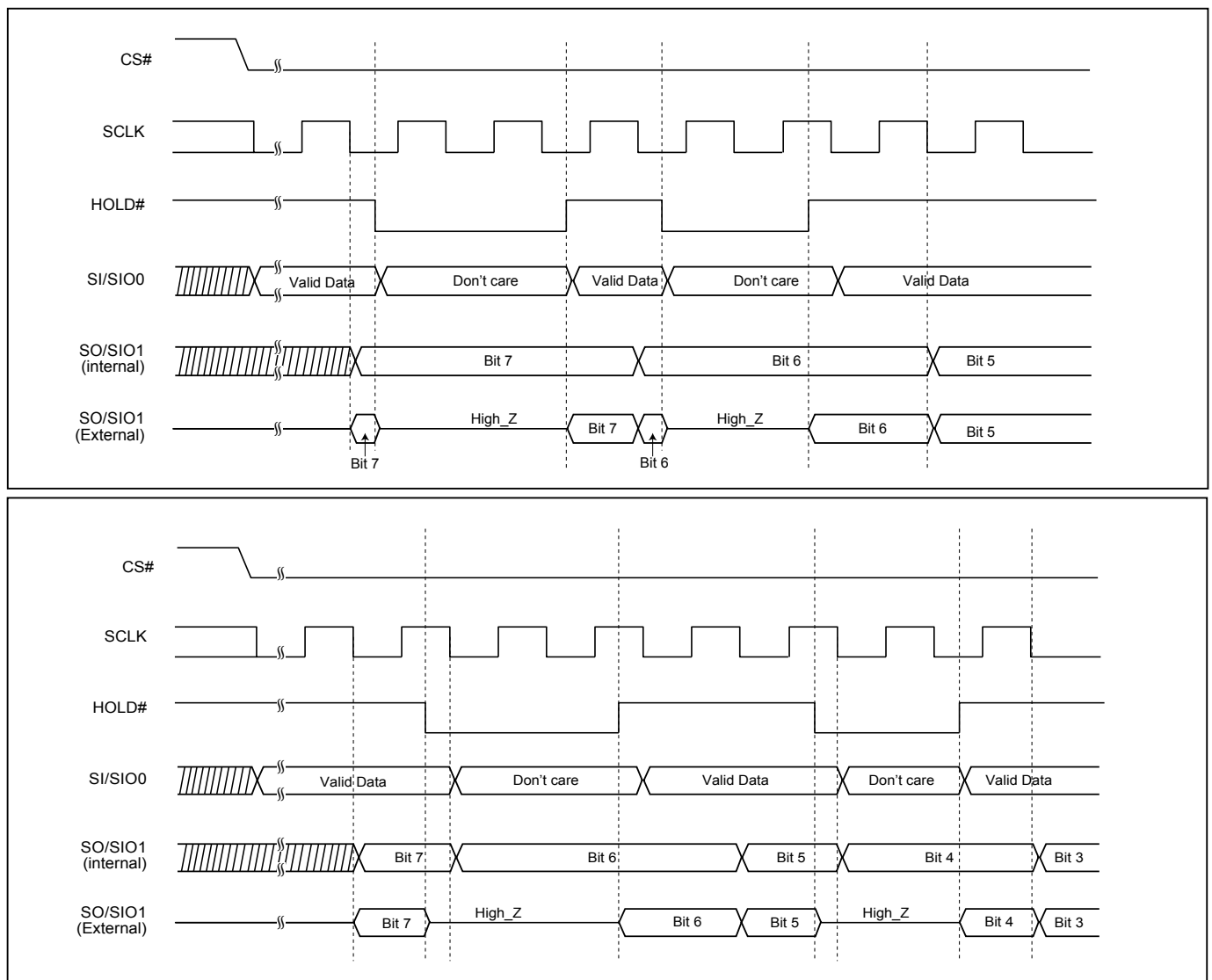


## 9. HOLD FEATURE

HOLD# pin signal goes low to hold any serial communications with the device. The HOLD feature will not stop the operation of write status register, programming, or erasing in progress.

The operation of HOLD requires Chip Select (CS#) keeping low and starts on falling edge of HOLD# pin signal while Serial Clock (SCLK) signal is being low (if Serial Clock signal is not being low, HOLD operation will not start until Serial Clock signal being low). The HOLD condition ends on the rising edge of HOLD# pin signal while Serial Clock(SCLK) signal is being low (if Serial Clock signal is not being low, HOLD operation will not end until Serial Clock being low).

**Figure 4. Hold Condition Operation**



During the HOLD operation, the Serial Data Output (SO) is high impedance when Hold# pin goes low and will keep high impedance until Hold# pin goes high. The Serial Data Input (SI) is don't care if both Serial Clock (SCLK) and Hold# pin goes low and will keep the state until SCLK goes low and Hold# pin goes high. If Chip Select (CS#) drives high during HOLD operation, it will reset the internal logic of the device. To re-start communication with chip, the HOLD# must be at high and CS# must be at low.

**Note:** The HOLD feature is disabled during Quad I/O mode.

**10. COMMAND DESCRIPTION**

**Table 5. Command Set**

**Read/Write Array Commands**

I/O	1	1	2	2	4	4
Command (byte)	READ (normal read)	FAST READ (fast read data)	2READ (2 x I/O read command)	DREAD (1I / 2O read command)	4READ (4 x I/O read)	QREAD (1I/4O read)
1st byte	03 (hex)	0B (hex)	BB (hex)	3B (hex)	EB (hex)	6B (hex)
2nd byte	ADD1	ADD1	ADD1	ADD1	ADD1	ADD1
3rd byte	ADD2	ADD2	ADD2	ADD2	ADD2	ADD2
4th byte	ADD3	ADD3	ADD3	ADD3	ADD3	ADD3
5th byte		Dummy	Dummy	Dummy	Dummy	Dummy
Action	n bytes read out until CS# goes high	n bytes read out until CS# goes high	n bytes read out by 2 x I/O until CS# goes high	n bytes read out by Dual Output until CS# goes high	Quad I/O read with 6 dummy cycles	n bytes read out by Quad output until CS# goes high

Mode	1	4	1	1	1	1	1
Command (byte)	PP (page program)	4PP (quad page program)	SE (sector erase)	BE 32K (block erase 32KB)	BE (block erase 64KB)	CE (chip erase)	RDSFDP (Read SFDP)
1st byte	02 (hex)	38 (hex)	20 (hex)	52 (hex)	D8 (hex)	60 or C7 (hex)	5A (hex)
2nd byte	ADD1	ADD1	ADD1	ADD1	ADD1		ADD1
3rd byte	ADD2	ADD2	ADD2	ADD2	ADD2		ADD2
4th byte	ADD3	ADD3	ADD3	ADD3	ADD3		ADD3
5th byte							Dummy
Action	to program the selected page	quad input to program the selected page	to erase the selected sector	to erase the selected 32KB block	to erase the selected block	to erase whole chip	Read SFDP mode

**Register/Setting Commands**

Command (byte)	WREN (write enable)	WRDI (write disable)	RDSR (read status register)	RDCR (read configuration register)	WRSR (write status register)	PGM/ERS Suspend (Suspends Program/Erase)
1st byte	06 (hex)	04 (hex)	05 (hex)	15 (hex)	01 (hex)	75 or B0 (hex)
2nd byte					Values	
3rd byte					Values	
4th byte					Values	
5th byte						
Action	sets the (WEL) write enable latch bit	resets the (WEL) write enable latch bit	to read out the values of the status register	to read out the values of the configuration register -1 & configuration register -2	to write new values of the configuration/status register	program/erase operation is interrupted by suspend command

Command (byte)	PGM/ERS Resume (Resumes Program/Erase)	DP (Deep power down)	SBL (Set Burst Length)
1st byte	7A or 30 (hex)	B9 (hex)	C0 (hex)
2nd byte			Value
3rd byte			
4th byte			
5th byte			
Action	to continue performing the suspended program/erase sequence	enters deep power down mode	to set Burst length

**ID/Reset Commands**

Command (byte)	RDID (read identification)	RES (read electronic ID)	REMS (read electronic manufacturer & device ID)	ENSO (enter secured OTP)	EXSO (exit secured OTP)	RDSCUR (read security register)	WRSCUR (write security register)
1st byte	9F (hex)	AB (hex)	90 (hex)	B1 (hex)	C1 (hex)	2B (hex)	2F (hex)
2nd byte		x	x				
3rd byte		x	x				
4th byte		x	ADD <i>(Note 1)</i>				
5th byte							
Action	outputs JEDEC ID: 1-byte Manufacturer ID & 2-byte Device ID	to read out 1-byte Device ID	output the Manufacturer ID & Device ID	to enter the 8K-bit secured OTP mode	to exit the 8K-bit secured OTP mode	to read value of security register	to set the lock-down bit as "1" (once lock-down, cannot be update)

COMMAND (byte)	NOP (No Operation)	RSTEN (Reset Enable)	RST (Reset Memory)	Release Read Enhanced
1st byte	00 (hex)	66 (hex)	99 (hex)	FF (hex)
2nd byte				
3rd byte				
4th byte				
5th byte				
Action			<i>(Note 3)</i>	All these commands FFh, 00h, AAh or 55h will escape the performance mode

Note 1: ADD=00H will output the manufacturer ID first and ADD=01H will output device ID first.

Note 2: It is not recommended to adopt any other code not in the command definition table, which will potentially enter the hidden mode.

Note 3: The RSTEN command must be executed before executing the RST command. If any other command is issued in-between RSTEN and RST, the RST command will be ignored.

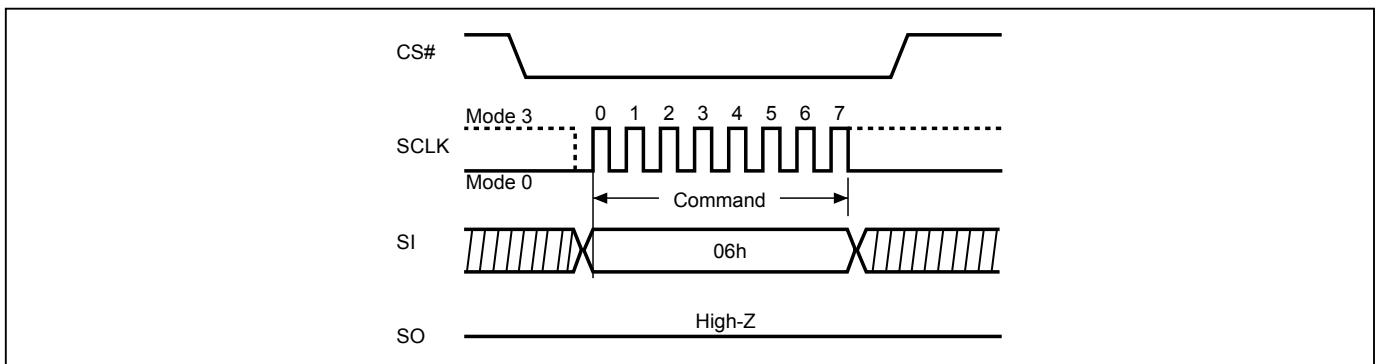
### 10-1. Write Enable (WREN)

The Write Enable (WREN) instruction is for setting Write Enable Latch (WEL) bit. For those instructions like PP, 4PP, SE, BE32K, BE, CE, and WRSR, which are intended to change the device content WEL bit should be set every time after the WREN instruction setting the WEL bit.

The sequence of issuing WREN instruction is: CS# goes low→sending WREN instruction code→ CS# goes high.

The SIO[3:1] are "don't care" .

**Figure 5. Write Enable (WREN) Sequence**



## 10-2. Write Disable (WRDI)

The Write Disable (WRDI) instruction is to reset Write Enable Latch (WEL) bit.

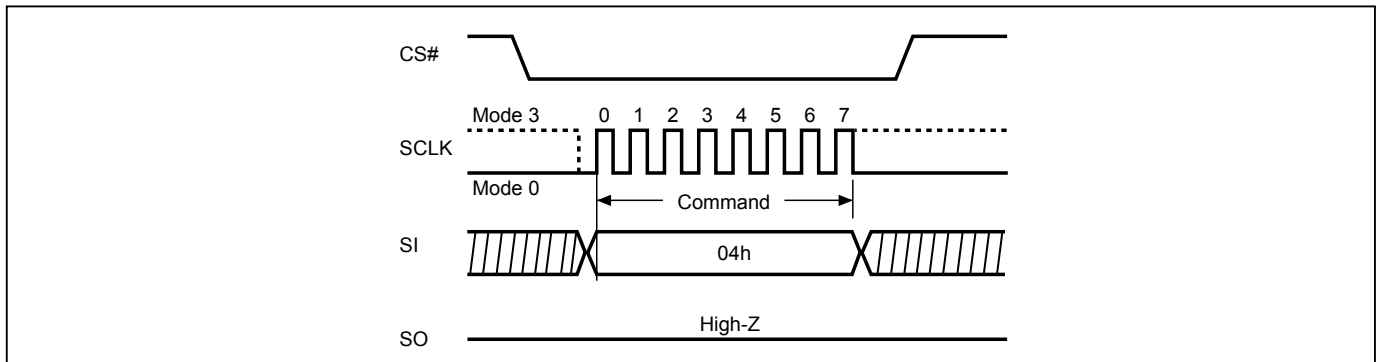
The sequence of issuing WRDI instruction is: CS# goes low→sending WRDI instruction code→CS# goes high.

The SIO[3:1] are "don't care".

The WEL bit is reset by following situations:

- Power-up
- Reset# pin driven low
- Completion of Write Disable (WRDI) instruction
- Completion of Write Status Register (WRSR) instruction
- Completion of Page Program (PP) instruction
- Completion of Quad Page Program (4PP) instruction
- Completion of Sector Erase (SE) instruction
- Completion of Block Erase 32KB(BE32K) instruction
- Completion of Block Erase (BE) instruction
- Completion of Chip Erase (CE) instruction
- Program/Erase Suspend
- Completion of Softreset command
- Completion of Write Security Register (WRSCUR) command

**Figure 6. Write Disable (WRDI) Sequence**



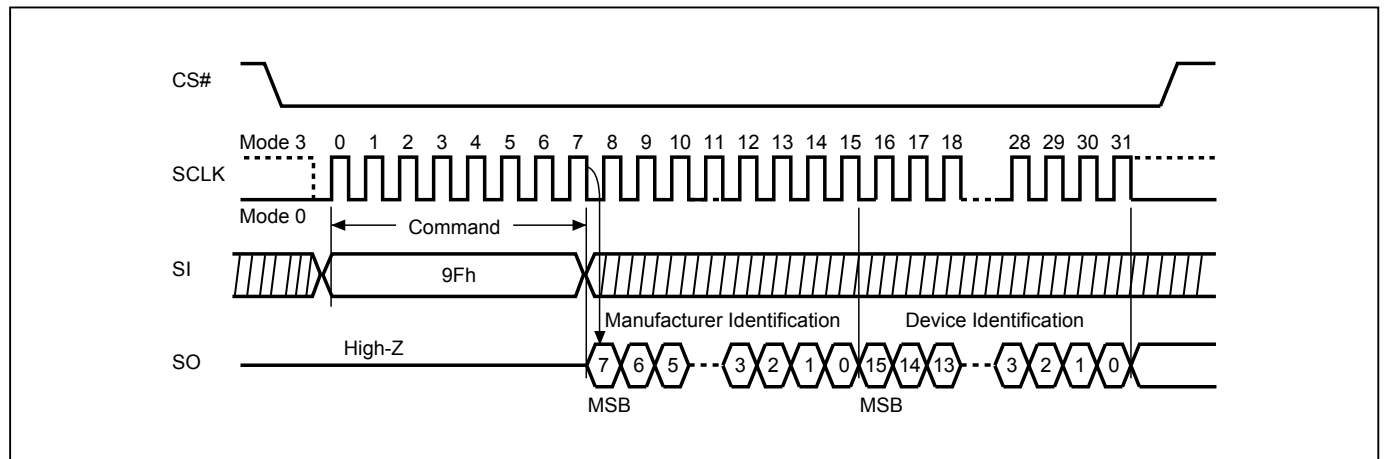
### 10-3. Read Identification (RDID)

The RDID instruction is for reading the manufacturer ID of 1-byte and followed by Device ID of 2-byte. The Macronix Manufacturer ID and Device ID are listed as "Table 6. ID Definitions".

The sequence of issuing RDID instruction is: CS# goes low→ sending RDID instruction code→24-bits ID data out on SO→ to end RDID operation can drive CS# to high at any time during data out.

While Program/Erase operation is in progress, it will not decode the RDID instruction, therefore there's no effect on the cycle of program/erase operation which is currently in progress. When CS# goes high, the device is at standby stage.

**Figure 7. Read Identification (RDID) Sequence**



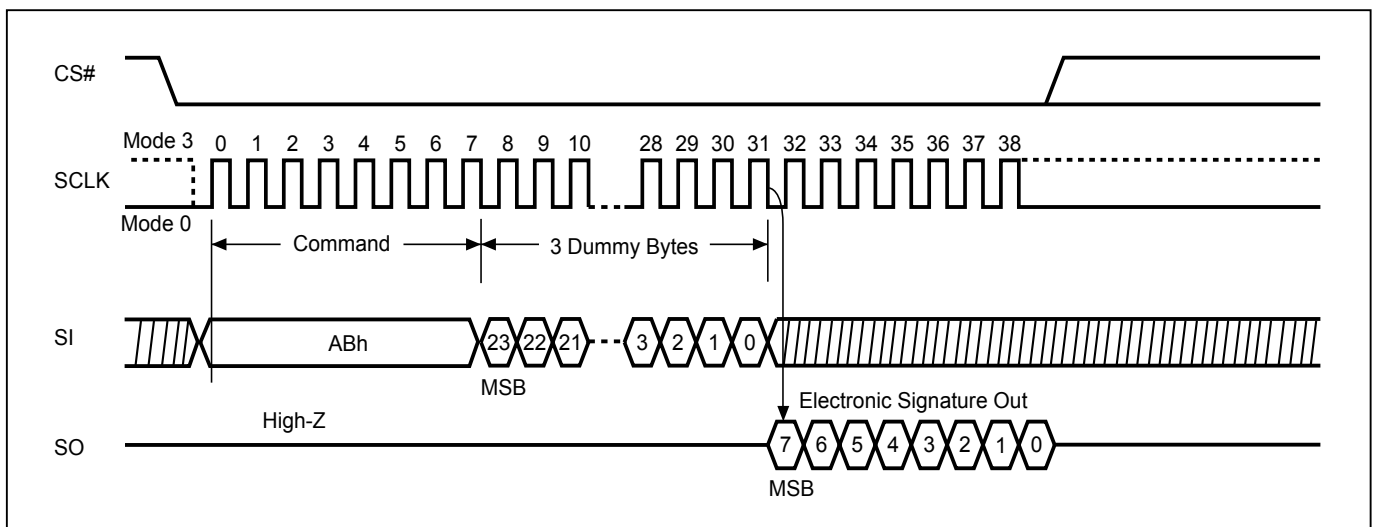
#### 10-4. Read Electronic Signature (RES)

RES instruction is for reading out the old style of 8-bit Electronic Signature, whose values are shown as "Table 6. ID Definitions". This is not the same as RDID instruction. It is not recommended to use for new design. For new design, please use RDID instruction.

The SIO[3:1] are "don't care".

The RES instruction is ended by CS# goes high after the ID been read out at least once. The ID outputs repeatedly if continuously send the additional clock cycles on SCLK while CS# is at low.

**Figure 8. Read Electronic Signature (RES) Sequence**



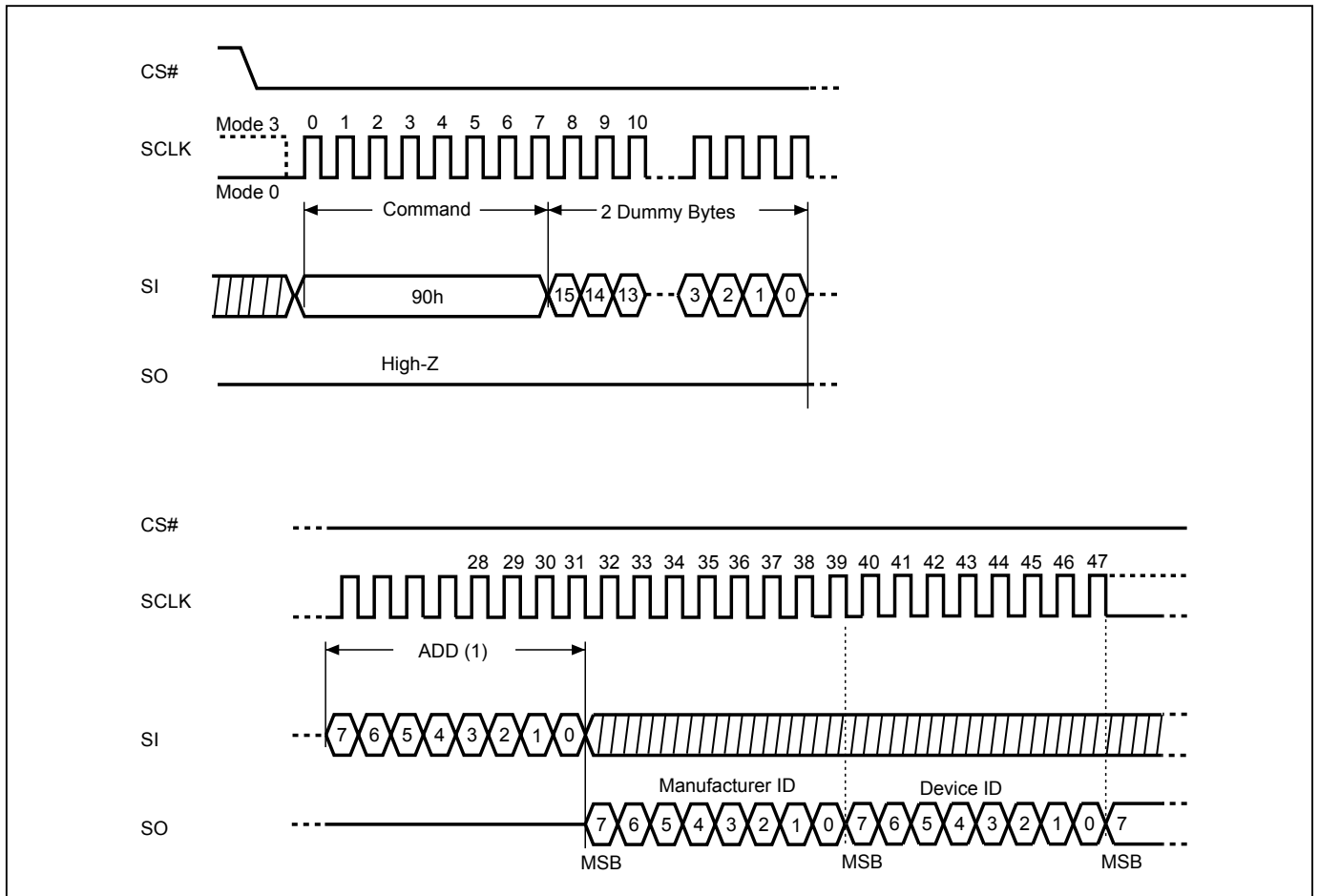


**10-5. Read Electronic Manufacturer ID & Device ID (REMS)**

The REMS instruction returns both the JEDEC assigned manufacturer ID and the device ID. The Device ID values are listed in "Table 6. ID Definitions".

The REMS instruction is initiated by driving the CS# pin low and sending the instruction code "90h" followed by two dummy bytes and one address byte (A7~A0). After which the manufacturer ID for Macronix (C2h) and the device ID are shifted out on the falling edge of SCLK with the most significant bit (MSB) first. If the address byte is 00h, the manufacturer ID will be output first, followed by the device ID. If the address byte is 01h, then the device ID will be output first, followed by the manufacturer ID. While CS# is low, the manufacturer and device IDs can be read continuously, alternating from one to the other. The instruction is completed by driving CS# high.

**Figure 9. Read Electronic Manufacturer & Device ID (REMS) Sequence**



**Notes:**

(1) ADD=00H will output the manufacturer's ID first and ADD=01H will output device ID first.

**10-6. ID Read**

User can execute this ID Read instruction to identify the Device ID and Manufacturer ID. The sequence of issuing RDID instruction is: CS# goes low→ sending RDID instruction code→24-bits ID data out on SO→ to end RDID operation can drive CS# to high at any time during data out.

After the command cycle, the device will immediately output data on the falling edge of SCLK. The manufacturer ID, memory type, and device ID data byte will be output continuously, until the CS# goes high.

While Program/Erase operation is in progress, it will not decode the RDID instruction, therefore there's no effect on the cycle of program/erase operation which is currently in progress. When CS# goes high, the device is at standby stage.

**Table 6. ID Definitions**

Command Type	Command	MX25R6435F		
		RDID	9Fh	Manufacturer ID C2
RES	ABh	Electronic ID 17		
REMS	90h	Manufacturer ID C2	Device ID 17	